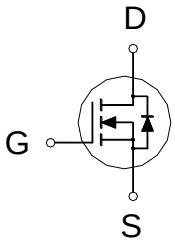
杰力科技股份有限公司
Excelliance MOS Corporation

EMB14N10H

N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	100V
$R_{DSON\ (MAX.)}$	16.5mΩ
I_D	44A



UIS, Rg 100% Tested

RoHS & Halogen Free & TSCA Compliant

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	44	A
	T_C = 100 °C		28	
Pulsed Drain Current[1]		I_{DM}	100	
Avalanche Current		I_{AS}	20	
Avalanche Energy	L = 0.1mH, ID=20A, RG=25Ω	E_{AS}	20	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	E_{AR}	10	
Power Dissipation	T_C = 25 °C	P_D	50	W
	T_C = 100 °C		20	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

100% UIS testing in condition of VD=50V, L=0.1mH, VG=10V, IL=12A, Rated VDS=100V N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle < 1%

[3]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

[4]Guarantee by Engineering test

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	2.0	3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} = 70V, V_{GS} = 0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	44			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		14	16.5	mΩ
		V_{GS} = 4.5V, I_D = 10A		16.5	21	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		42		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		4505		pF
Output Capacitance	C_{oss}			195		
Reverse Transfer Capacitance	C_{rss}			44		
Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz		1.6		Ω
Total Gate Charge[1,2]	Q_g	V_{DS} = 50V, V_{GS} = 10V, I_D = 20A		64		nC
Gate-Source Charge[1,2]	Q_{gs}			15		
Gate-Drain Charge[1,2]	Q_{gd}			11		
Turn-On Delay Time[1,2]	$t_{d(on)}$	V_{DS} = 50V, I_D = 5A, V_{GS} = 10V, R_G = 6Ω		20		nS
Rise Time[1,2]	t_r			20		
Turn-Off Delay Time[1,2]	$t_{d(off)}$			50		
Fall Time[1,2]	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I_S				44	A
Pulsed Current[3]	I_{SM}				100	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A / μS		30		nS
Reverse Recovery Charge	Q_{rr}			130		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB14N10H for EDFN 5 x 6

B14N10: Device Name

ABCDEFG: Date Code

A: Assembly House

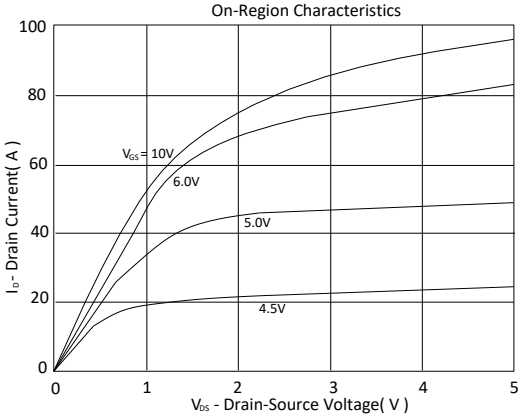
B: Year(A:2008 B:2009 C:2010….)

C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)

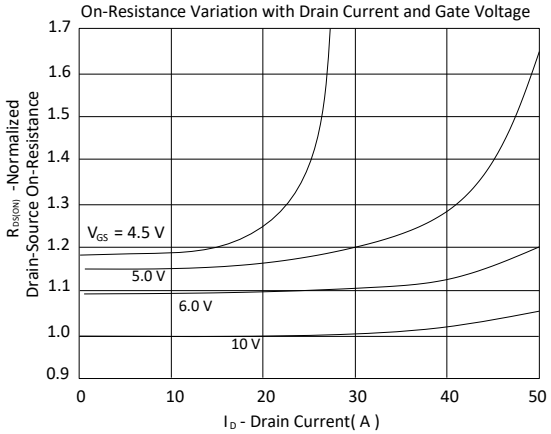
DEFG: Serial No.

TYPICAL CHARACTERISTICS

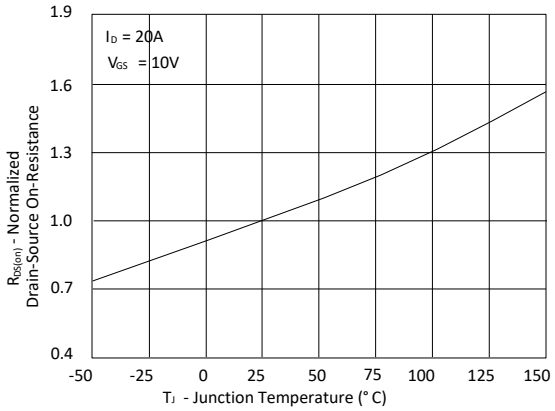
On-Region Characteristics



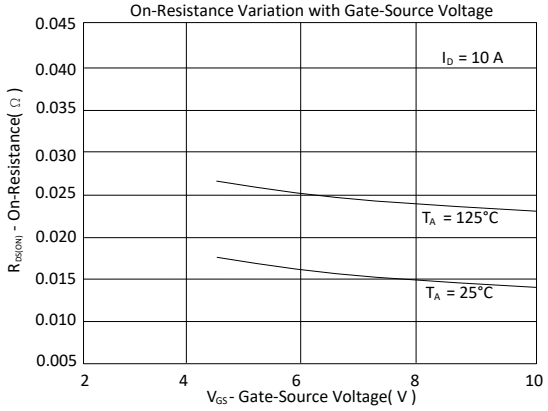
On-Resistance Variation with Drain Current and Gate Voltage



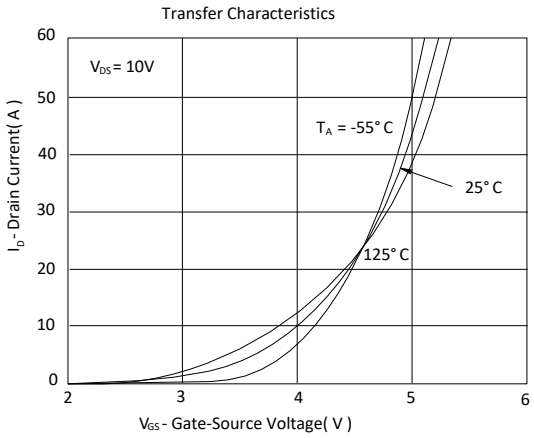
On-Resistance Variation with Temperature



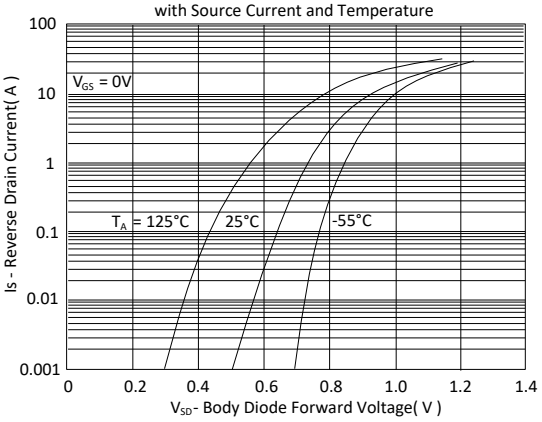
On-Resistance Variation with Gate-Source Voltage



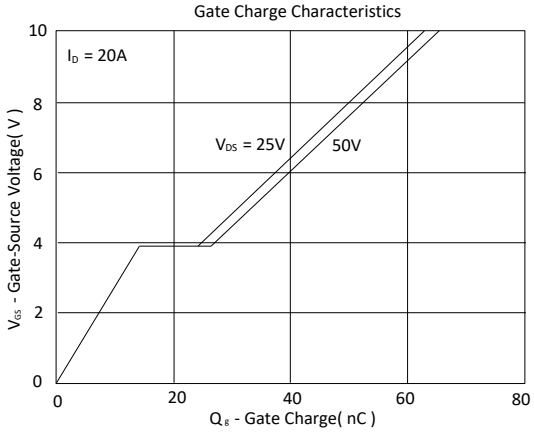
Transfer Characteristics



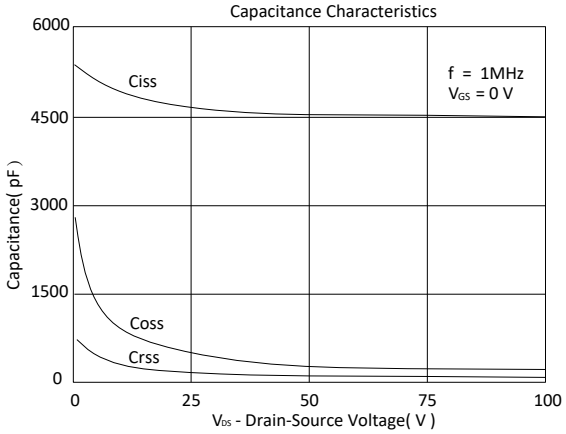
Body Diode Forward Voltage Variation
with Source Current and Temperature



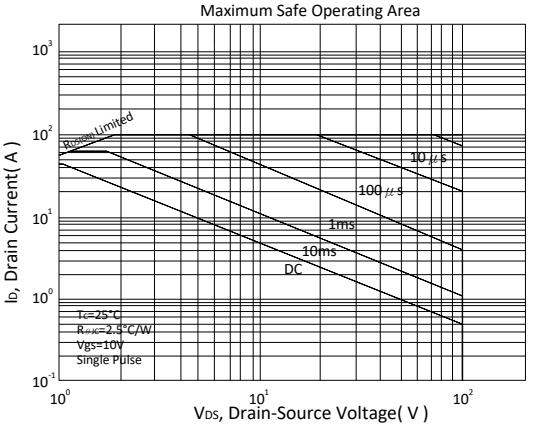
Gate Charge Characteristics



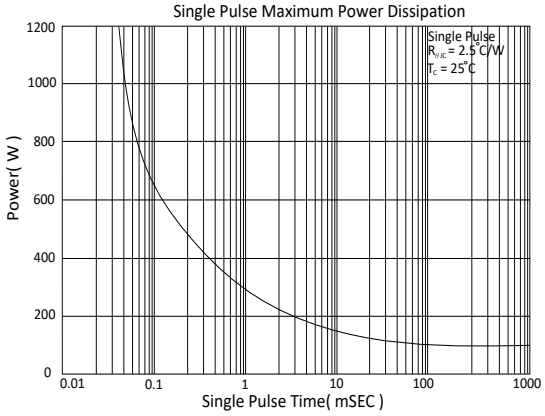
Capacitance Characteristics



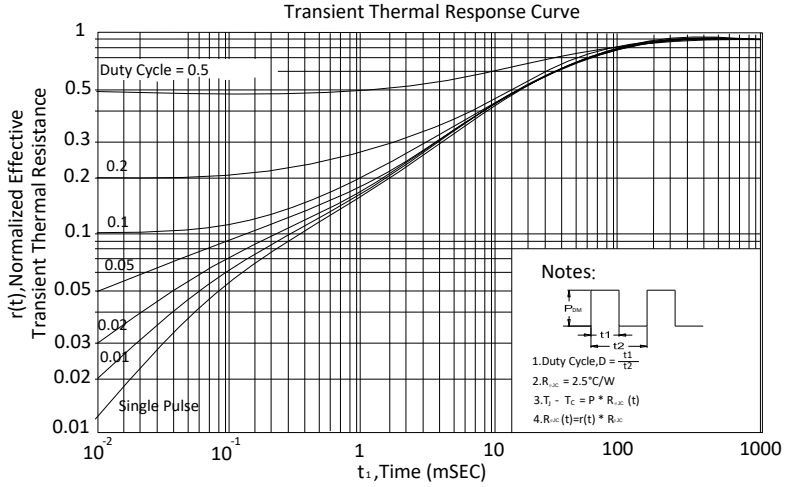
Maximum Safe Operating Area



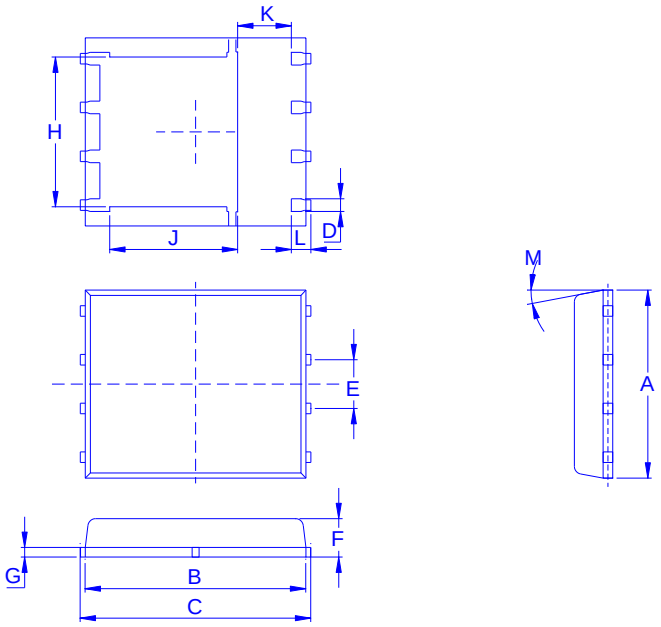
Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



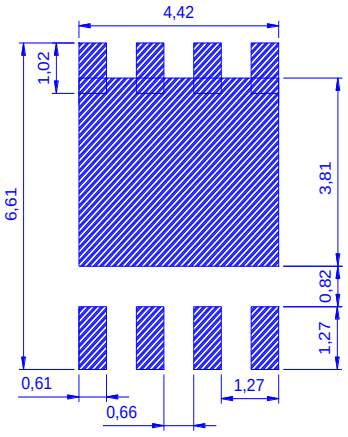
Outline Drawing



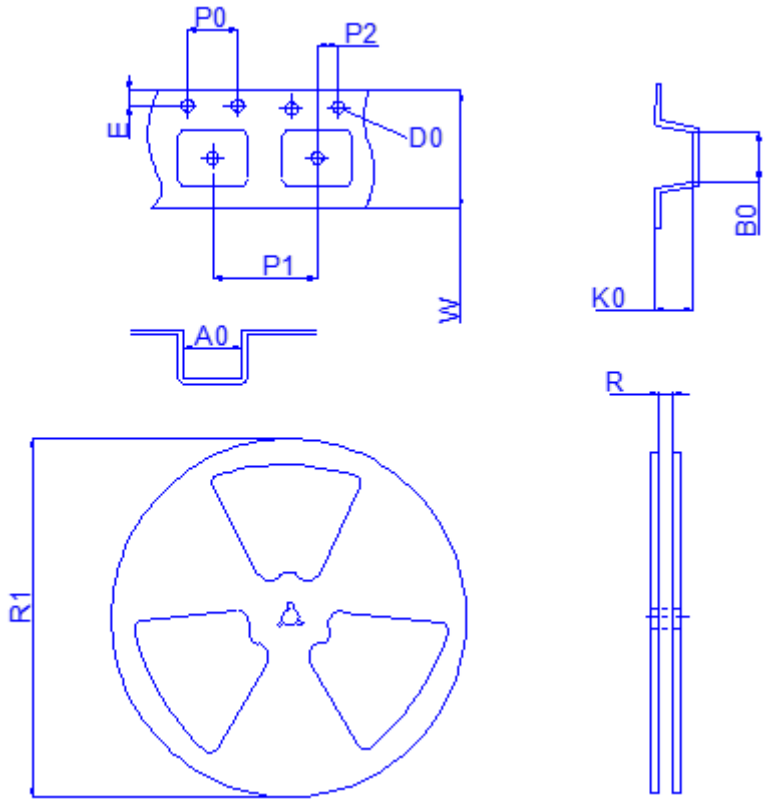
Dimension in mm

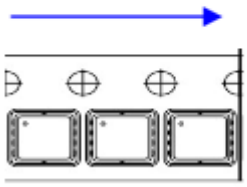
Dimension	A	B	C	D	E	F	G	H	J	K	L	M
Min	4.8	5.55	5.9	0.3	1.17	0.85	0.15	3.61	3.18	1	0.38	0°
Typ.	4.9	5.7	6	0.4	1.27	0.95	0.2	3.87	3.44	1.2	0.4	
Max	5.4	5.85	6.15	0.51	1.37	1.17	0.34	4.31	3.78	1.39	0.71	12°

Recommended minimum pads



Tape&Reel Information:2500pcs/Reel



Package	EDFN5X6
Reel	13"
Device orientation	FEED DIRECTION 

Dimension in mm

Dimension	Carrier tape									Reel	
	A0	B0	D0	E	K0	P0	P1	P2	W	R	R1
Typ.	6.4	5.3	1.5	1.8	1.6	4	8	2	12	12.4	330
±	0.2	0.2	0.1	0.1	0.6	0.1	0.1	0.1	0.3	2	2